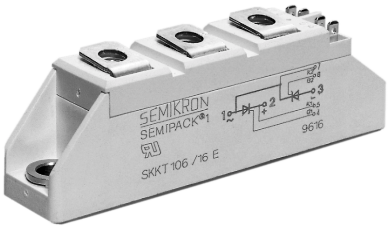
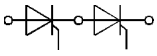
V_{RSM}	V_{RRM}	(dv/	I_{TRMS} (maximum value for continuous operation)			
	V_{DRM}	$dt)_{cr}$	50 A			
			I_{TAV} (sin. 180; T_{case} = 68 °C)			
V	V	V/µs	32 A			
500	400	500	–	–	**SKKH 26/04 D**	–
700	600	500	**SKKT 26/06 D**	–	**SKKH 26/06 D**	**SKKH 27/06 D**
900	800	500	**SKKT 26/08 D**	**SKKT 27/08 D**[1)]	**SKKH 26/08 D**	**SKKH 27/08 D**
1300	1200	1000	**SKKT 26/12 E**	**SKKT 27/12 E**[1)]	**SKKH 26/12 E**	**SKKH 27/12 E**
1500	1400	1000	**SKKT 26/14 E**	**SKKT 27/14 E**[1)]	**SKKH 26/14 E**	**SKKH 27/14 E**
1700	1600	1000	**SKKT 26/16 E**	**SKKT 27/16 E**[1)]	**SKKH 26/16 E**	**SKKH 27/16 E**
1900	1800	1000	**SKKT 26/18 E**	–	–	**SKKH 27/18 E**

Symbol	**Conditions**		**SKKT 26 SKKH 26**	**SKKT 27 SKKT 27B SKKH 27**	**Units**
I_{TAV}	sin. 180;	T_{case} = 68 °C	32		A
		T_{case} = 85 °C	25		A
I_D	B2/B6	T_{amb} = 45 °C; P 3/180	38 / 50		A
		T_{amb} = 35 °C; P 3/180 F	60 / 77		A
I_{RMS}	W1/W3	T_{amb} = 45 °C; P 3/180	52 / 3 x 37		A
I_{TSM}	T_{vj} = 25 °C; 10 ms		550		A
	T_{vj} = 125 °C; 10 ms		480		A
i^2t	T_{vj} = 25 °C; 8,3 ... 10 ms		1 500		A^2s
	T_{vj} = 125 °C; 8,3 ... 10 ms		1 150		A^2s
t_{gd}	T_{vj} = 25 °C; I_G = 1 A				
		di_G/dt = 1 A/µs	1		µs
t_{gr}	$V_D = 0{,}67 \cdot V_{DRM}$		1		µs
$(di/dt)_{cr}$	T_{vj} = 125 °C		150		A/µs
t_q	T_{vj} = 125 °C		typ. 80		µs
I_H	T_{vj} = 25 °C; typ./max.		100 / 200		mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ./max.		250 / 400		mA
V_T	T_{vj} = 25 °C; I_T = 75 A		max. 1,8		V
$V_{T(TO)}$	T_{vj} = 125 °C		0,9		V
r_T	T_{vj} = 125 °C		12		mΩ
I_{DD}; I_{RD}	T_{vj} = 125 °C;	$V_{RD} = V_{RRM}$			
		$V_{DD} = V_{DRM}$	max. 10		mA
V_{GT}	T_{vj} = 25 °C; d.c.		3		V
I_{GT}	T_{vj} = 25 °C; d.c.		150		mA
V_{GD}	T_{vj} = 125 °C; d.c.		0,25		V
I_{GD}	T_{vj} = 125 °C; d.c.		5		mA
R_{thjc}	cont.	per thyristor / per module	0,9 / 0,45		°C/W
	sin. 180		0,95 / 0,48		°C/W
	rec. 120		1,0 / 0,5		°C/W
R_{thch}			0,2 / 0,1		°C/W
T_{vj}			– 40 ... + 125		°C
T_{stg}			– 40 ... + 125		°C
V_{isol}	a. c. 50 Hz; r.m.s; 1 s/1 min		3600 / 3000		V~
M_1	to heatsink	SI (US) units	5 (44 lb. in.) ± 15 %[2)]		Nm
M_2	to terminals	SI (US) units	3 (26 lb. in.) ± 15 %		Nm
a			$5 \cdot 9{,}81$		m/s^2
w	approx.		95		g
Case	→ page B 1 – 95	SKKT 26: A 5 SKKH 26: A 6	SKKT 27: A 46 SKKT 27B: A 48 SKKH 27: A 47		

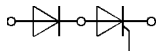
SEMIPACK® 1
Thyristor / Diode Modules

SKKT 26 SKKH 26
SKKT 27 SKKH 27
SKKT 27B

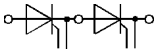




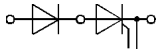
SKKT 26



SKKH 26



SKKT 27
SKKT 27B



SKKH 27

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

Typical Applications

- DC motor control (e.g. for machine tools)
- AC motor soft starters
- Temperature control (e.g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

[1)] Also available in SKKT 27B configuration (case A 48)
[2)] See the assembly instructions

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

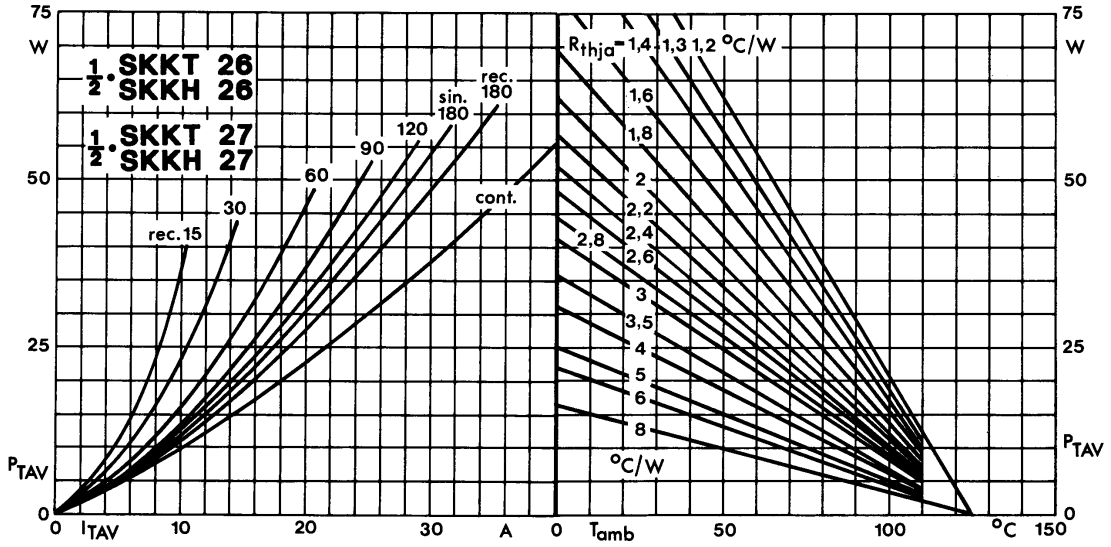


Fig. 1 Power dissipation per thyristor vs. on-state current and ambient temperature

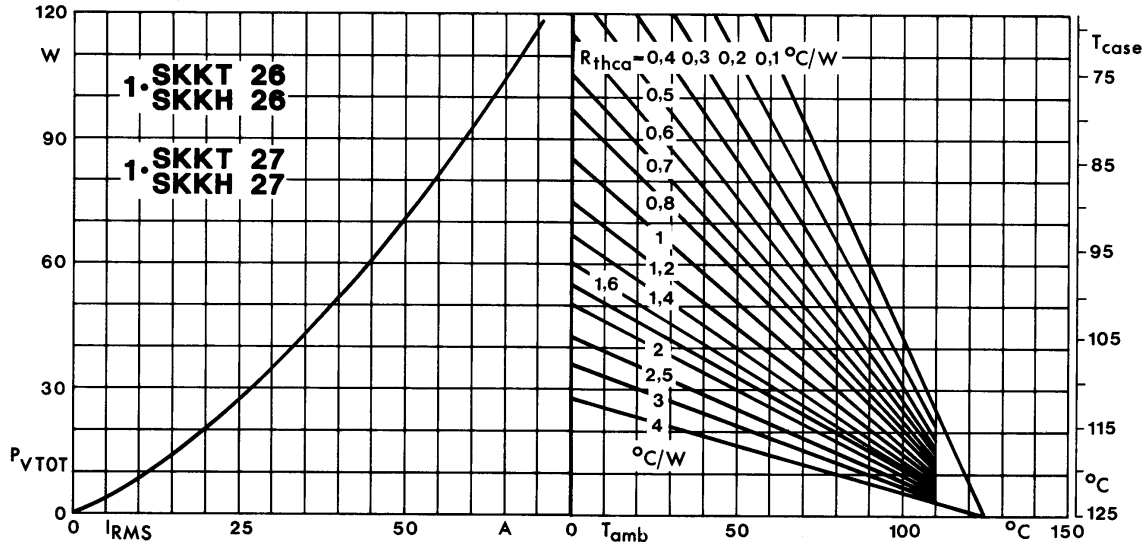


Fig. 2 Power dissipation per module vs. rms current and case temperature

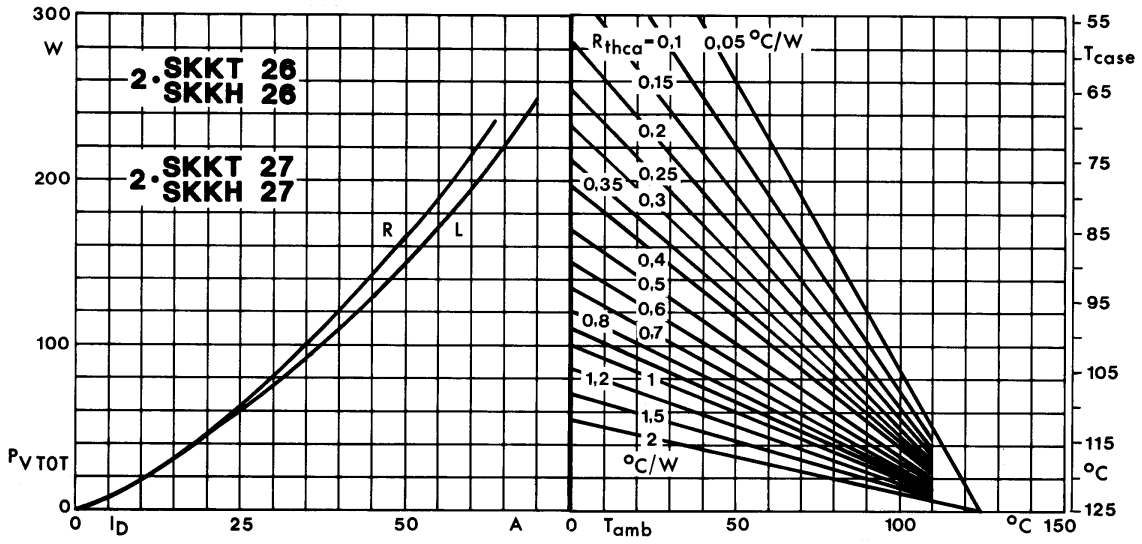


Fig. 3 Power dissipation of two modules vs. direct current and case temperature

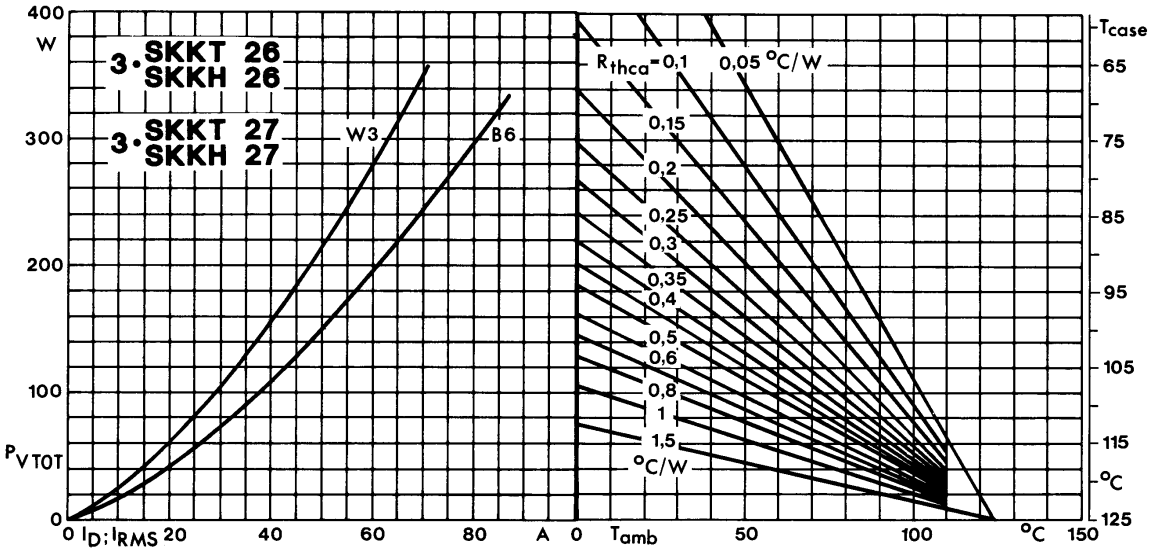


Fig. 4 Power dissipation of three modules vs. direct and rms current and case temperature

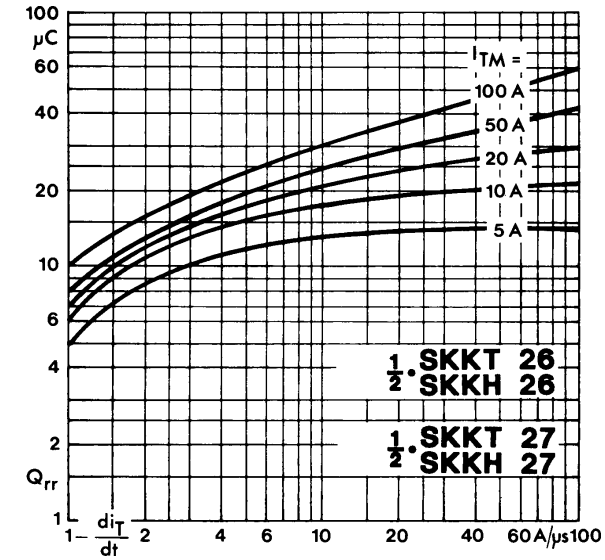


Fig. 5 Recovered charge vs. current decrease

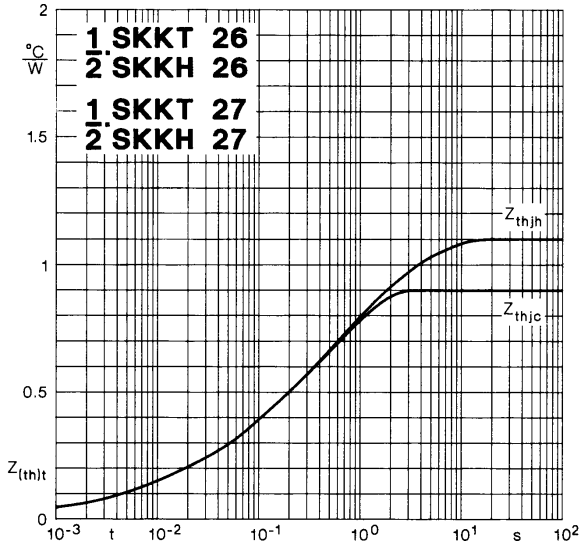


Fig. 6 Transient thermal impedance vs. time

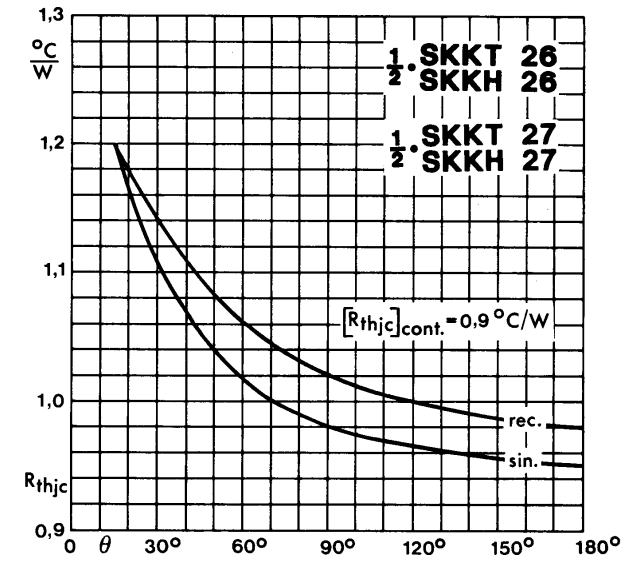


Fig. 7 Thermal resistance vs. conduction angle

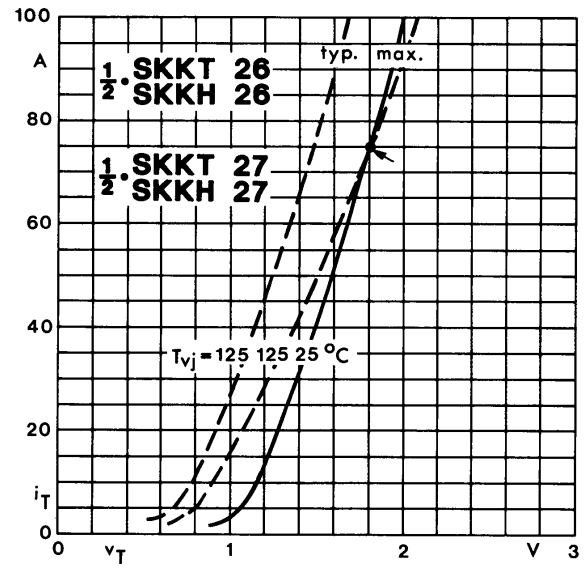


Fig. 8 On-state characteristics

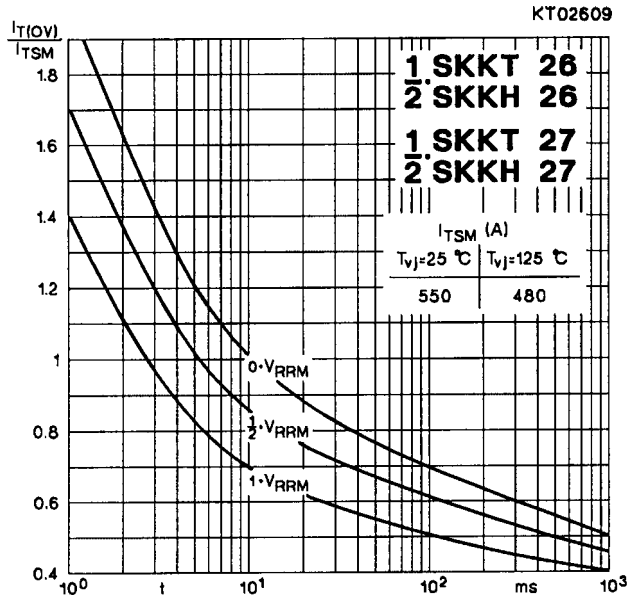


Fig. 9 Surge overload current vs. time

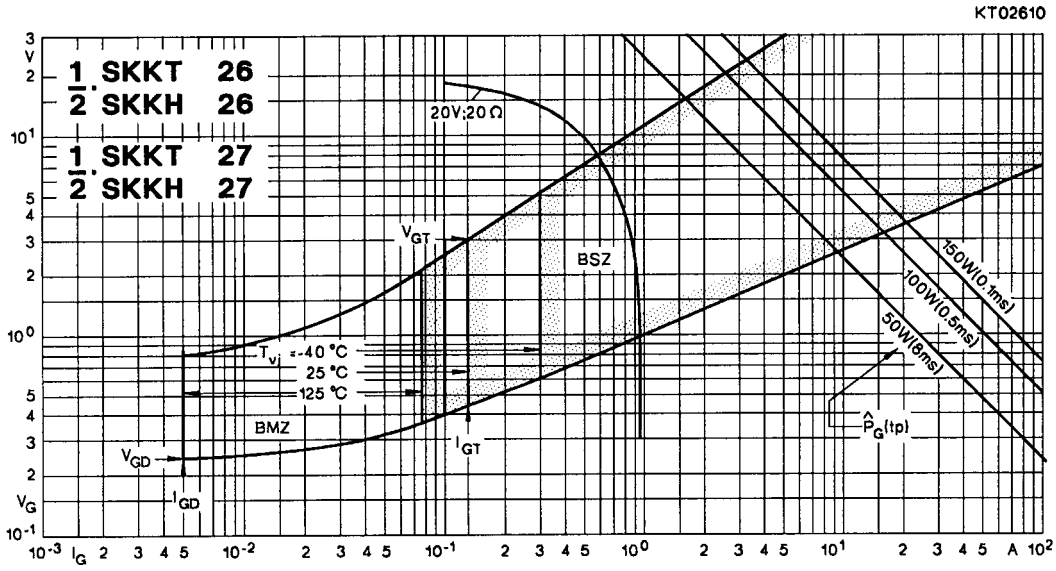


Fig. 10 Gate trigger characteristics

